

Serial No. 10/574,556
Filing Date: April 3, 2006

Customer No. 26,289
Attorney's Docket No. 2003JP322

Remarks

The Examiner has rejected claims 1-4, 6, 7, 10, 12-18 under 35 USC 102 (b), as being anticipated by or, in the alternative, under 35 USC 103(a) as obvious over Tashiro (JP 2002-293941) in view of Babich et al (US 5,141,817). The Examiner has also rejected claims 8, 9 and 11 under 35 USC 103(a) as being unpatentable over Tashiro (JP 2002-293941) in view of Uchimarui et al (US 2002/0142533).

Claim 5 has been amended. Claims 1-4 and 6-18 have been canceled.

The amended claim 5 now specifically refers to a process for producing a semiconductor device, comprising the steps of: forming an insulating layer and an etching stopper layer on a substrate; removing part of the insulating layer by dry etching; and filling an electrically conductive material into a groove or hole thus formed, wherein said etching stopper layer is formed by curing a composition comprising a silicon-containing polymer, wherein 5% to 100% by mole, based on the total number of moles of silicon contained in the silicon-containing polymer, of silicon is contained in a disilylbenzene structure, further where the silicon-containing polymer has a carbon content of not less than 30% by weight, and further where the etching stopper layer is cured at a temperature in the range of 200°C to 500°C for 30 to 50 minutes.

Support for the amendment to claim 5 is present in the specification in paragraph [0034].

Neither Tashiro nor Babich disclose a process for producing a semiconductor device, comprising the steps of: forming an insulating layer and an etching stopper layer on a substrate; removing part of the insulating layer by

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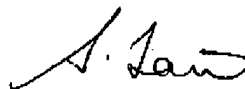
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dry etching; and filling an electrically conductive material into a groove or hole thus formed, wherein said etching stopper layer is formed, and specifically where the etching stopper layer is cured at a temperature in the range of 200°C to 500°C for 30 to 50 minutes.

In view of the above amendments and remarks, the present application is believed to be in condition for allowance, and reconsideration of it is requested. If the Examiner disagrees, she is requested to contact the attorney for Applicants at the telephone number provided below.

Respectfully submitted,



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